

REMARKS

The rejection of claims 1, 3-4, 8, 10-13 and 15-16 under 35 USC 103(a) as being unpatentable over Dhote et al (USP 5,777,356) is respectfully traversed.

The present invention is directed to a method for preparing a film structure of a ferroelectric single crystal, useful in the fabrication of many electric and electronic devices comprising forming a layer of material having a perovskite single crystal substrate. Moreover, the Examiner's kind attention is directed to the fact that claim 1 has been amended to clearly define the substrate on which an electrode layer of a material having a perovskite crystal structure is formed with the method for preparing the ferroelectric film structure being characterized by using a ferroelectric single crystal substrate having an off-axis crystal structure, or a silicon single crystal substrate having a metal oxide layer of perovskite crystal structure on the surface thereof, as a substrate; and onto the substrate, forming a layer of a material having a perovskite crystal structure as an electrode layer.

The combination of steps provided in claim 1 results in the beneficial effect that the single crystal can be grown epitaxially having improved properties.

The Dhote '356 patent cited by the Examiner, on the other hand, relates to a platinum-free ferroelectric memory cell with intermetallic barrier. As already recognized by the Examiner, the '356 patent is limited solely to the teaching of a metal oxide electrode layer deposited on a silicon substrate. Stated otherwise, the '356 patent discloses neither the use of the substrate in a method for preparing a film

structure of a ferroelectric single crystal or the formation of an electrode layer having a perovskite crystal structure for use in a method as claimed.

Accordingly, the Dhote et al patent does not teach or suggest the present invention as now recited in amended claim 1 and the rejection under 35 USC 103 should be withdrawn.

Claims 3-4, 8, 10-13 and 15-16 are dependent claims, which are considered patentable for the same reasons as given above.

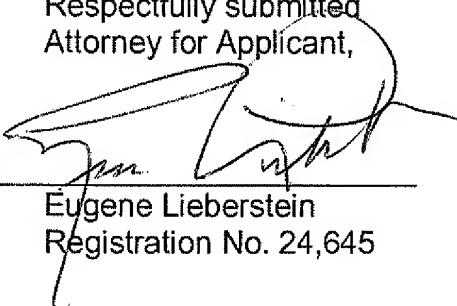
Reconsideration and allowance of claims remaining in the present application is respectfully solicited.

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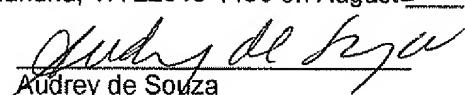
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CERTIFICATE OF EFS-WEB TRANSMISSION

I hereby certify that this Amendment is being submitted via EFS-Web and is addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on August 30, 2007.


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